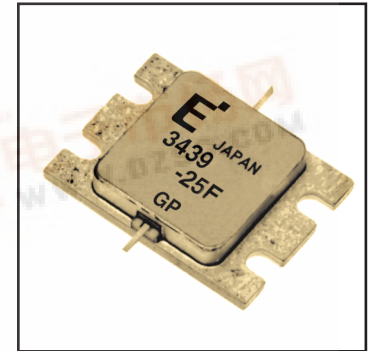


# FLM3439-25F

## C-Band Internally Matched FET

### FEATURES

- High Output Power:  $P_{1dB} = 44.5\text{dBm}$  (Typ.)
- High Gain:  $G_{1dB} = 10.5\text{dB}$  (Typ.)
- High PAE:  $\eta_{add} = 41\%$  (Typ.)
- Low  $IM_3 = -46\text{dBc}$  @  $P_o = 33.5\text{dBm}$
- Broad Band: 3.4 ~ 3.9GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



### DESCRIPTION

The FLM3439-25F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

### ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_C = 25^\circ\text{C}$	93.7	W
Storage Temperature	$T_{stg}$		-65 to +175	$^\circ\text{C}$
Channel Temperature	$T_{ch}$		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 64.0 and -11.2 mA respectively with gate resistance of 25 $\Omega$ .

### ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	11.6	17.4	A
Transconductance	$g_m$	$V_{DS} = 5\text{V}, I_{DS} = 6.8\text{A}$	-	5800	-	mS
Pinch-off Voltage	$V_p$	$V_{DS} = 5\text{V}, I_{DS} = 600\text{mA}$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -600\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DS} = 10\text{V},$ $I_{DS} = 0.55 I_{DSS}$ (Typ.), $f = 3.4 \sim 3.9 \text{GHz},$ $Z_S = Z_L = 50 \text{ohm}$	43.5	44.5	-	dBm
Power Gain at 1dB G.C.P.	$G_{1dB}$		9.5	10.5	-	dB
Drain Current	$I_{dsr}$		-	6200	7600	mA
Power-added Efficiency	$\eta_{add}$		-	41	-	%
Gain Flatness	$\Delta G$		-	-	$\pm 0.6$	dB
3rd Order Intermodulation Distortion	$IM_3$	$f = 3.9 \text{GHz}, \Delta f = 10 \text{MHz}$ 2-Tone Test $P_{out} = 33.5\text{dBm S.C.L.}$	-44	-46	-	dBc
Thermal Resistance	$R_{th}$	Channel to Case	-	1.4	1.6	$^\circ\text{C/W}$
Channel Temperature Rise	$\Delta T_{ch}$	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	100	$^\circ\text{C}$

CASE STYLE: IK

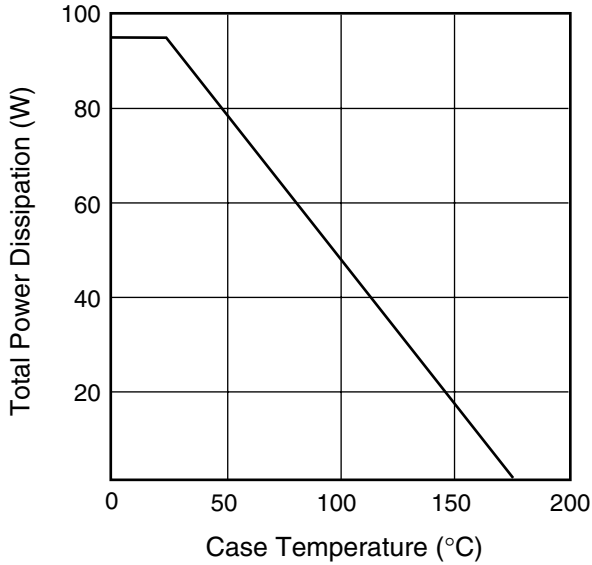
G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level



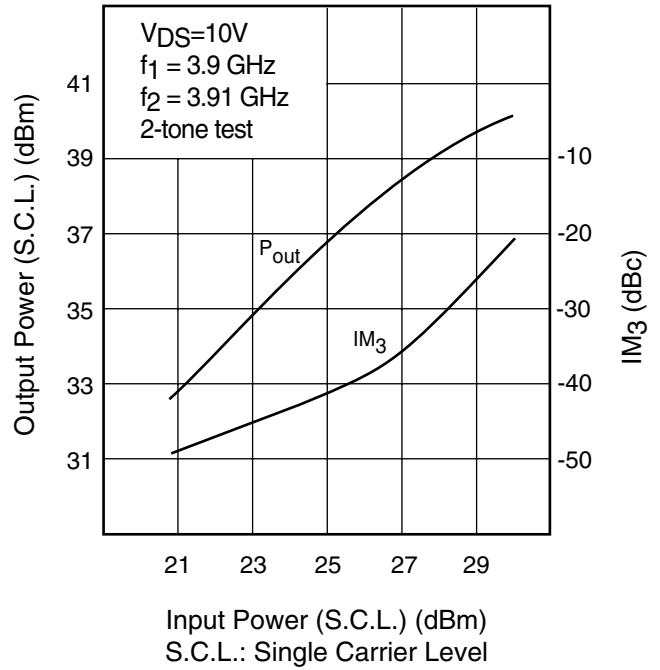
# FLM3439-25F

C-Band Internally Matched FET

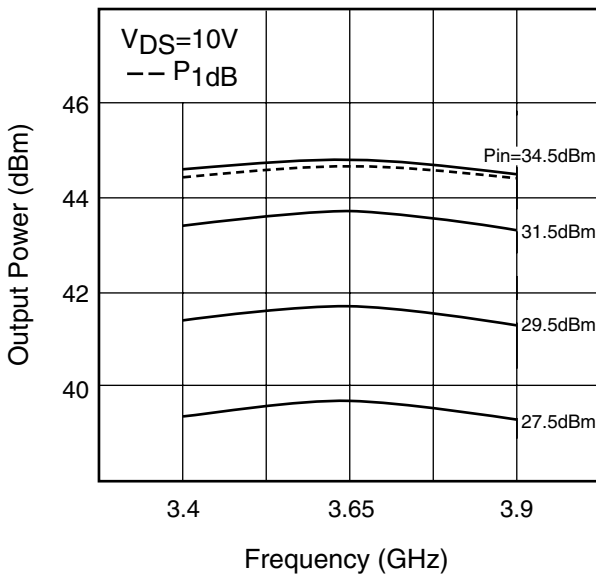
### POWER DERATING CURVE



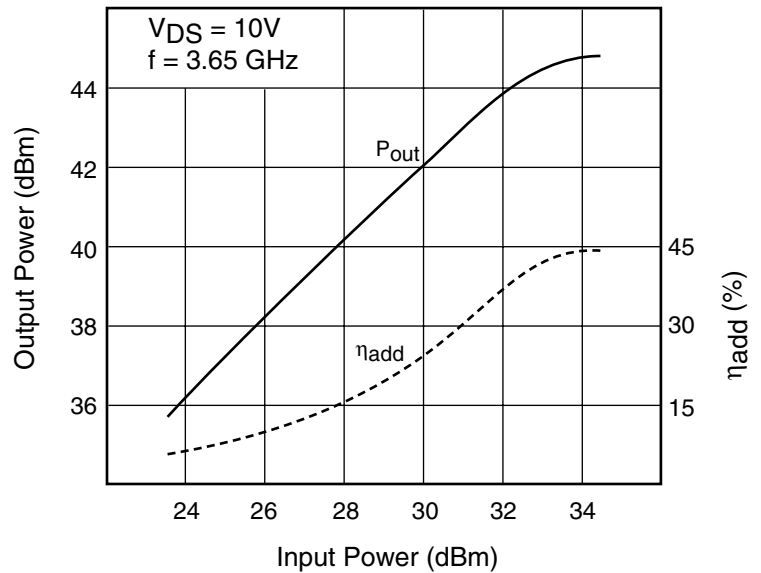
### OUTPUT POWER & IM<sub>3</sub> vs. INPUT POWER



### OUTPUT POWER vs. FREQUENCY

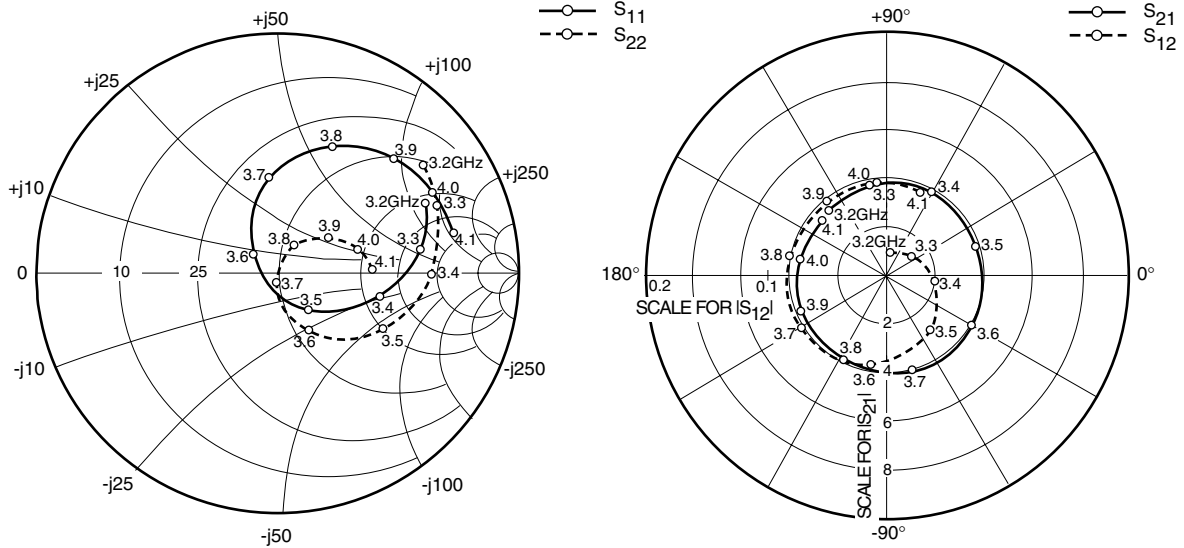


### OUTPUT POWER vs. INPUT POWER



# FLM3439-25F

## C-Band Internally Matched FET



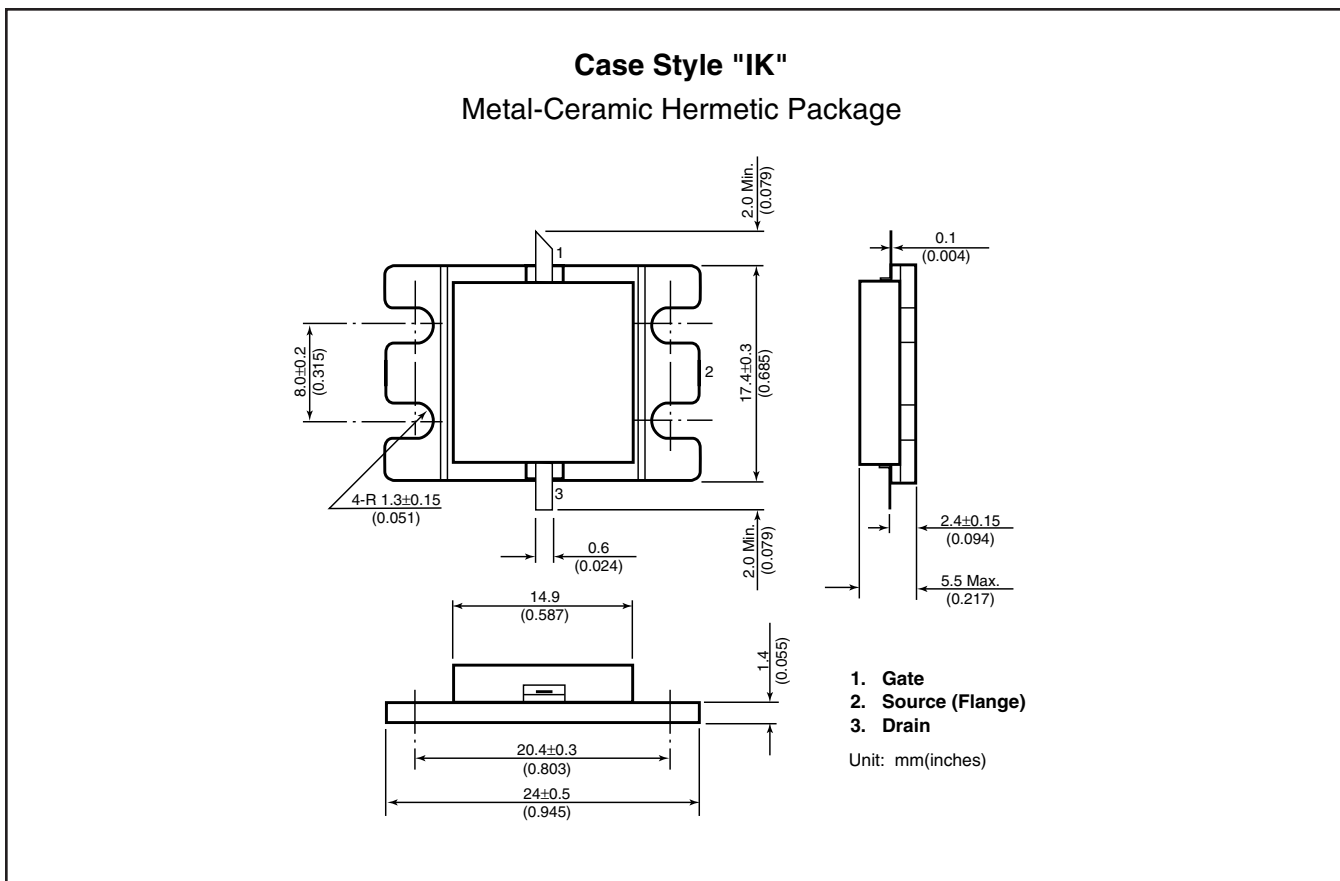
### S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 6800mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
3200	.675	25.7	3.631	132.1	.018	81.3	.753	37.0
3300	.591	9.8	3.802	101.4	.025	38.7	.709	22.3
3400	.440	-14.5	3.936	61.7	.039	-6.7	.631	-0.5
3500	.198	-50.0	3.799	17.8	.058	-52.4	.493	-28.9
3600	.130	139.2	4.074	-29.2	.075	-101.5	.273	-62.6
3700	.403	95.0	4.027	-76.3	.083	-148.7	.046	-105.4
3800	.582	67.2	3.981	-118.4	.083	169.3	.134	62.2
3900	.679	45.1	3.890	-157.6	.079	130.4	.262	36.4
4000	.721	27.6	3.631	168.3	.076	96.9	.343	16.2
4100	.739	13.4	3.508	139.8	.073	68.8	.397	1.2

# FLM3439-25F

## C-Band Internally Matched FET



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### CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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